

TITLEs of most frequently occurring classifications of patents returned
from a search of 10598123 on Mar 09, 2010

- 6 136/ 249 (4 OR, 2 XR)
 Class 136 BATTERIES: THERMOELECTRIC AND PHOTOELECTRIC
 136/243 .. PHOTOELECTRIC
 136/244 .. Panel or array
 136/249 .. Monolithic semiconductor
- 4 365/ 201 (3 OR, 1 XR)
 Class 365 STATIC INFORMATION STORAGE AND RETRIEVAL
 365/189.011 .. READ/WRITE CIRCUIT
 365/201 .. Testing
- 3 438/ 396 (3 OR, 0 XR)
 Class 438 SEMICONDUCTOR DEVICE MANUFACTURING PROCESS
 438/381 .. MAKING PASSIVE DEVICES (E.G., RESISTOR, CAPACITOR, ETC.)
 438/396 .. Stacked capacitor
- 3 429/ 185 (0 OR, 3 XR)
 Class 429 CHEMISTRY: ELECTRICAL CURRENT PRODUCING APPARATUS, PRODUCT, AND PROCESS
 429/122 .. CURRENT PRODUCING CELL, ELEMENTS, SUBCOMBINATIONS AND COMPOSITIONS FOR USE THEREWITH AND ADJUNCTS
 429/163 .. Cell enclosure structure, e.g., housing, casing, container, cover, etc.
 429/185 .. Having seal feature
- 3 438/ 933 (0 OR, 3 XR)
 Class 438 SEMICONDUCTOR DEVICE MANUFACTURING PROCESS
 438/933 .. GERMANIUM OR SILICON OR GE-SI-ON III-V
- 3 438/ 74 (1 OR, 2 XR)
 Class 438 SEMICONDUCTOR DEVICE MANUFACTURING PROCESS
 438/48 .. MAKING DEVICE OR CIRCUIT RESPONSIVE TO NON-ELECTRICAL SIGNAL
 438/57 .. Responsive to electromagnetic radiation
 438/73 .. Making electromagnetic responsive array
 438/74 .. Vertically arranged (e.g., tandem stacked, etc.)
- 2 257/ 461 (0 OR, 2 XR)
 Class 257 ACTIVE SOLID-STATE DEVICES (E.G., TRANSISTORS, SOLID-STATE DIODES)
 257/414 .. RESPONSIVE TO NON-ELECTRICAL SIGNAL (E.G., CHEMICAL, STRESS, LIGHT, OR MAGNETIC FIELD SENSORS)
 257/428 .. Electromagnetic or particle radiation
 257/431 .. Light
 257/461 .. Light responsive junction
- 2 712/ 15 (2 OR, 0 XR)
 Class 712 ELECTRICAL COMPUTERS AND DIGITAL PROCESSING SYSTEMS: PROCESSING ARCHITECTURES AND INSTRUCTION PROCESSING (E.G., PROCESSORS)
 712/ 1 .. PROCESSING ARCHITECTURE
 712/ 10 .. Array processor
 712/ 11 .. Array processor element interconnection
 712/ 15 .. Reconfiguring
- 2 438/ 970 (0 OR, 2 XR)
 Class 438 SEMICONDUCTOR DEVICE MANUFACTURING PROCESS
 438/970 .. SPECIFIED ETOH STOP MATERIAL
- 2 257/ E27.089 (0 OR, 2 XR)
 Class 257 ACTIVE SOLID-STATE DEVICES (E.G., TRANSISTORS, SOLID-STATE

DIODES)

257/ E27. 001 . . . DEVI CE CONSISTI NG OF A PLURALITY OF SEM CONDUCTOR OR OTHER SOLI D STATE COMPOUNDS FORMED IN OR ON A COMMON SUBSTRATE, E. G., INTEGRATED CI RCUIT DEVI CE (EPO)

257/ E27. 009 . . . Includi ng semi conductor component with at least one potential barrier or surface barrier adapted for rectifying, oscillating, amplifying, or switching, or Includi ng integrated passive circuit elements (EPO)

257/ E27. 01 . . . Wth semi conductor substrate only (EPO)

257/ E27. 07 . . . Includi ng a plurality of individual components in a repetitive configuration (EPO)

257/ E27. 081 . . . Includi ng field-effect component (EPO)

257/ E27. 084 . . . Dynam ic random access memory, DRAM structure (EPO)

257/ E27. 085 . . . One-transistor memory cell structure, i. e., each memory cell containing only one transistor (EPO)

257/ E27. 086 . . . Storage electrode stacked over the transistor

257/ E27. 089 . . . Storage electrode having multiple wings (EPO)

2 365/ 63 (0 OR, 2 XR)

Cl ass 365 STATIC INFORMATION STORAGE AND RETRIEVAL

365/ 63 . . . INTERCONNECTI ON ARRANGEMENTS

2 438/ 586 (0 OR, 2 XR)

Cl ass 438 SEM CONDUCTOR DEVI CE MANUFACTURING PROCESS

438/ 584 . . . COATING WTH ELECTRI CALLY OR THERMALLY CONDUCTIVE MATERIAL

438/ 585 . . . Insul ated gate formation

438/ 586 . . . Combi ned wth formation of ohmic contact to semi conductor region

2 257/ E27. 101 (0 OR, 2 XR)

Cl ass 257 ACTIVE SOLI D-STATE DEVI CES (E. G., TRANSISTORS, SOLI D-STATE

DIODES)

257/ E27. 001 . . . DEVI CE CONSISTI NG OF A PLURALITY OF SEM CONDUCTOR OR OTHER SOLI D STATE COMPOUNDS FORMED IN OR ON A COMMON SUBSTRATE, E. G., INTEGRATED CI RCUIT DEVI CE (EPO)

257/ E27. 009 . . . Includi ng semi conductor component with at least one potential barrier or surface barrier adapted for rectifying, oscillating, amplifying, or switching, or Includi ng integrated passive circuit elements (EPO)

257/ E27. 01 . . . Wth semi conductor substrate only (EPO)

257/ E27. 07 . . . Includi ng a plurality of individual components in a repetitive configuration (EPO)

257/ E27. 081 . . . Includi ng field-effect component (EPO)

257/ E27. 098 . . . Static random access memory, SRAM structure (EPO)

257/ E27. 101 . . . Load element being a resistor (EPO)

2 429/ 59 (1 OR, 1 XR)

Cl ass 429 CHEM STRY: ELECTRI CAL CURRENT PRODUCI NG APPARATUS, PRODUCT, AND PROCESS

429/ 57 . . . SEALED CELL HAVING GAS PREVENTI ON OR ELIMI NATION MEANS

429/ 59 . . . Prevention or elimination means is one of the cell electrodes or is electrically connected to an electrode

2 429/ 157 (1 OR, 1 XR)

Cl ass 429 CHEM STRY: ELECTRI CAL CURRENT PRODUCI NG APPARATUS, PRODUCT, AND PROCESS

429/ 122 . . . CURRENT PRODUCI NG CELL, ELEMENTS, SUBCOMBINATI ONS AND

COMPOSITI ONS FOR USE THEREW TH AND ADJUNCTS

429/ 149 . . . Plural cells

429/ 156 . . . Complete cells

429/ 157 . . . In end-to-end contact, e. g., stacked button-type cell, et c.

2 429/ 162 (0 OR, 2 XR)

Cl ass 429 CHEM STRY: ELECTRI CAL CURRENT PRODUCI NG APPARATUS, PRODUCT,

AND PROCESS

429/122 . CURRENT PRODUCING CELL, ELEMENTS, SUBCOMBINATIONS AND COMPOSITIONS FOR USE THEREWITH AND ADJUNCTS
 429/162 . Flat-type unit cell and specific unit cell components

2 429/210 (0 OR, 2 XR)
 Class 429 CHEM STRY: ELECTRICAL CURRENT PRODUCING APPARATUS, PRODUCT, AND PROCESS

429/122 . CURRENT PRODUCING CELL, ELEMENTS, SUBCOMBINATIONS AND COMPOSITIONS FOR USE THEREWITH AND ADJUNCTS
 429/209 . Electrode
 429/210 . Bipolar type

2 429/90 (0 OR, 2 XR)
 Class 429 CHEM STRY: ELECTRICAL CURRENT PRODUCING APPARATUS, PRODUCT, AND PROCESS
 429/90 . WITH MEASURING, TESTING, OR INDICATING MEANS

2 429/217 (0 OR, 2 XR)
 Class 429 CHEM STRY: ELECTRICAL CURRENT PRODUCING APPARATUS, PRODUCT, AND PROCESS
 429/122 . CURRENT PRODUCING CELL, ELEMENTS, SUBCOMBINATIONS AND COMPOSITIONS FOR USE THEREWITH AND ADJUNCTS
 429/209 . Electrode
 429/212 . Having active material with organic component
 429/217 . . . Organic component is a binder

2 429/223 (1 OR, 1 XR)
 Class 429 CHEM STRY: ELECTRICAL CURRENT PRODUCING APPARATUS, PRODUCT, AND PROCESS
 429/122 . CURRENT PRODUCING CELL, ELEMENTS, SUBCOMBINATIONS AND COMPOSITIONS FOR USE THEREWITH AND ADJUNCTS
 429/209 . Electrode
 429/218.1 . . . Chemically specified inorganic electrochemically active material containing
 429/223 . . . Nickel component is active material

2 257/E27.129 (0 OR, 2 XR)
 Class 257 ACTIVE SOLID-STATE DEVICES (E.G., TRANSISTORS, SOLID-STATE DIODES)
 257/E27.001 . DEVICE CONSISTING OF A PLURALITY OF SEMICONDUCTOR OR OTHER SOLID-STATE COMPONENTS FORMED IN OR ON A COMMON SUBSTRATE, E.G., INTEGRATED CIRCUIT DEVICE (EPO)

257/E27.122 . . . including active semiconductor component sensitive to infrared radiation, light, or electromagnetic radiation of a shorter wavelength (EPO)

257/E27.127 . . . Device controlled by radiation (EPO)
 257/E27.128 . . . With at least one potential barrier or surface barrier (EPO)
 257/E27.129 . . . In a repetitive configuration (EPO)

2 257/E31.115 (0 OR, 2 XR)
 Class 257 ACTIVE SOLID-STATE DEVICES (E.G., TRANSISTORS, SOLID-STATE DIODES)
 257/E31.001 . SEMICONDUCTOR DEVICES RESPONSIVE OR SENSITIVE TO ELECTROMAGNETIC RADIATION (E.G., INFRARED RADIATION, ADAPTED FOR CONVERSION OF RADIATION INTO ELECTRICAL ENERGY OR FOR CONTROL OF ELECTRICAL ENERGY BY SUCH RADIATION PROCESSES, OR APPARATUS PECULIAR TO MANUFACTURE OR TREATMENT OF SUCH DEVICES, OR OF PARTS THEREOF) (EPO)

257/E31.11 . . . Detail of nonsemiconductor component of radiation-sensitive semiconductor device (EPO)
 257/E31.113 . . . Circuit arrangement of general character for device (EPO)
 257/E31.114 . . . For device having potential or surface barrier (EPO)

257/ E31. 115 Position-sensitive and lateral-effect photodetector
(e. g., quadrant photodiode) (EPO)

2 257/ E27. 128 (0 OR, 2 XR)
Class 257 ACTIVE SOLID-STATE DEVICES (E. G., TRANSISTORS, SOLID-STATE
DIODES)

257/ E27. 001 DEVICES CONSISTING OF A PLURALITY OF SEMICONDUCTOR OR OTHER
SOLID-STATE COMPONENTS FORMED IN OR ON A COMMON SUBSTRATE, E. G., INTEGRATED CIRCUIT
DEVICES (EPO)

257/ E27. 122 including active semiconductor component sensitive to
infrared radiation, light, or electromagnetic radiation of a shorter wavelength
(EPO)

257/ E27. 127 Device controlled by radiation (EPO)

257/ E27. 128 With at least one potential barrier or surface barrier
(EPO)

2 429/ 218. 1 (0 OR, 2 XR)
Class 429 CHEMISTRY: ELECTRICAL CURRENT PRODUCING APPARATUS, PRODUCT,
AND PROCESS

429/ 122 CURRENT PRODUCING CELL, ELEMENTS, SUBCOMBINATIONS AND
COMPOSITIONS FOR USE THEREWITH AND ADJUNCTS

429/ 209 Electrode

429/ 218. 1 Chemically specified inorganic electrochemically active
material containing

2 716/ 8 (1 OR, 1 XR)
Class 716 DATA PROCESSING: DESIGN AND ANALYSIS OF CIRCUIT OR
SEM CONDUCTOR MASK

716/ 1 CIRCUIT DESIGN

716/ 8 Floor planning

2 204/ 252 (0 OR, 2 XR)
Class 204 CHEMISTRY: ELECTRICAL AND WAVE ENERGY

204/ 193 . . . APPARATUS

204/ 194 . . . Electrolytic

204/ 242 . . . Cells

204/ 252 . . . Diaphragm type

2 429/ 337 (0 OR, 2 XR)
Class 429 CHEMISTRY: ELECTRICAL CURRENT PRODUCING APPARATUS, PRODUCT,
AND PROCESS

429/ 122 CURRENT PRODUCING CELL, ELEMENTS, SUBCOMBINATIONS AND
COMPOSITIONS FOR USE THEREWITH AND ADJUNCTS

429/ 188 include electrolyte chemically specified and method

429/ 324 Chemically specified organic solvent containing

429/ 336 Hetero ring in the organic solvent

429/ 337 Oxygen is the only ring hetero atom in the hetero ring

(e. g., dioxolane, gamma butyrolactone, etc.)

2 438/ 73 (1 OR, 1 XR)
Class 438 SEM CONDUCTOR DEVICE MANUFACTURING PROCESS

438/ 48 MAKING DEVICES OR CIRCUIT RESPONSIVE TO NONELECTRICAL SIGNALS

438/ 57 Responsive to electromagnetic radiation

438/ 73 Making electromagnetic responsive array

2 257/ E25. 007 (0 OR, 2 XR)
Class 257 ACTIVE SOLID-STATE DEVICES (E. G., TRANSISTORS, SOLID-STATE
DIODES)

257/ E25. 001 ASSEMBLIES CONSISTING OF PLURALITY OF INDIVIDUAL
SEM CONDUCTOR OR OTHER SOLID-STATE DEVICES (EPO)

257/ E25. 002 All devices being of same type, e. g., assemblies of
rectifier diodes (EPO)

257/ E25. 003 Devices not having separate carriers (EPO)

257/ E25. 004 Devices responsive or sensitive to electromagnetic radiation, e.g., infrared radiation, adapted for conversion of radiation into electrical energy or for control of electrical energy by such radiation (EPO)
 257/ E25. 006 Stacked arrangements of devices (EPO)
 257/ E25. 007 Devices being solar cells (EPO)

2 136/ 262 (0 OR, 2 XR)

Class 136 BATTERIES: THERMOELECTRIC AND PHOTOELECTRIC
 136/ 243 PHOTOELECTRIC
 136/ 252 Cells
 136/ 262 Gallium containing

2 257/ E31. 014 (0 OR, 2 XR)

Class 257 ACTIVE SOLID-STATE DEVICES (E.G., TRANSISTORS, SOLID-STATE DIODES)

257/ E31. 001 SEMICONDUCTOR DEVICES RESPONSIVE OR SENSITIVE TO ELECTROMAGNETIC RADIATION (E.G., INFRARED RADIATION, ADAPTED FOR CONVERSION OF RADIATION INTO ELECTRICAL ENERGY OR FOR CONTROL OF ELECTRICAL ENERGY BY SUCH RADIATION PROCESSES, OR APPARATUS PECULIAR TO MANUFACTURE OR TREATMENT OF SUCH DEVICES, OR OF PARTS THEREOF) (EPO)

257/ E31. 002 Characterized by semiconductor body (EPO)
 257/ E31. 003 Characterized by semiconductor body material (EPO)
 257/ E31. 004 Inorganic materials (EPO)
 257/ E31. 011 Including, apart from doping material or other impurity, only Group I-V element (EPO)
 257/ E31. 014 Characterized by doping material (EPO)

2 257/ E31. 021 (0 OR, 2 XR)

Class 257 ACTIVE SOLID-STATE DEVICES (E.G., TRANSISTORS, SOLID-STATE DIODES)

257/ E31. 001 SEMICONDUCTOR DEVICES RESPONSIVE OR SENSITIVE TO ELECTROMAGNETIC RADIATION (E.G., INFRARED RADIATION, ADAPTED FOR CONVERSION OF RADIATION INTO ELECTRICAL ENERGY OR FOR CONTROL OF ELECTRICAL ENERGY BY SUCH RADIATION PROCESSES, OR APPARATUS PECULIAR TO MANUFACTURE OR TREATMENT OF SUCH DEVICES, OR OF PARTS THEREOF) (EPO)

257/ E31. 002 Characterized by semiconductor body (EPO)
 257/ E31. 003 Characterized by semiconductor body material (EPO)
 257/ E31. 004 Inorganic materials (EPO)
 257/ E31. 019 Including, apart from doping material or other impurity, only Group III-V compound (EPO)
 257/ E31. 02 For device having potential or surface barrier (EPO)
 257/ E31. 021 Characterized by doping material GaAlAs, InGaAs, InGaAsP (EPO)

2 438/ 94 (0 OR, 2 XR)

Class 438 SEMICONDUCTOR DEVICE MANUFACTURING PROCESS
 438/ 48 MAKING DEVICE OR CIRCUIT RESPONSIVE TO NONELECTRICAL SIGNAL
 438/ 57 Responsive to electromagnetic radiation
 438/ 93 Compound semiconductor
 438/ 94 Heterojunction